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TISP4C115H3BJ THRU TISP4C350H3BJ

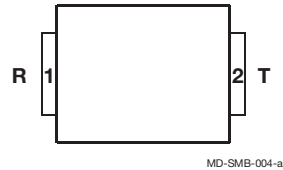
LOW CAPACITANCE
BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

TISP4CxxxH3BJ Overvoltage Protector Series

- Ion-Implanted Breakdown Region**
- Precise and Stable Voltage
 - Low Voltage Overshoot under Surge
 - Low Off-State Capacitance

| Device Name | V _{DRM} V | V _(BO) V |
|-----------------|-----------------------|------------------------|
| TISP4C115H3BJ † | 90 | 115 |
| TISP4C125H3BJ † | 100 | 125 |
| TISP4C145H3BJ † | 120 | 145 |
| TISP4C165H3BJ | 135 | 165 |
| TISP4C180H3BJ † | 145 | 180 |
| TISP4C220H3BJ † | 180 | 220 |
| TISP4C250H3BJ † | 190 | 250 |
| TISP4C290H3BJ † | 220 | 290 |
| TISP4C350H3BJ † | 275 | 350 |

SMB Package (Top View)



Device Symbol



Rated for International Surge Wave Shapes

| Wave Shape | Standard | I _{PPSM} A |
|------------|------------------|------------------------|
| 2/10 | GR-1089-CORE | 500 |
| 10/160 | TIA-968-A | 200 |
| 10/700 | ITU-T K.20/21/45 | 150 |
| 10/560 | TIA-968-A | 100 |
| 10/1000 | GR-1089-CORE | 100 |

..... **UL Recognized Component**

Description

This device is designed to limit overvoltages on the telephone line. Overvoltages are normally caused by a.c. power system or lightning flash disturbances which are induced or conducted on to the telephone line. A single device provides 2-point protection and is typically used for the protection of 2-wire telecommunication equipment (e.g. between the Ring and Tip wires for telephones and modems). Combinations of devices can be used for multi-point protection (e.g. 3-point protection between Ring, Tip and Ground).

The protector consists of a symmetrical voltage-triggered bidirectional thyristor. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. The high crowbar holding current helps prevent d.c. latchup as the diverted current subsides.

Please contact your Bourns representative if the protection voltage you require is not listed.

How to Order

| Device | Package | Carrier | Order As | Marking Code | Std. Qty. |
|---------------|---------|----------------------|------------------|--------------|-----------|
| TISP4CxxxH3BJ | SMB | Embossed Tape Reeled | TISP4CxxxH3BJR-S | 4CxxxH | 3000 |

Insert xxx corresponding to device name.

SEPTEMBER 2004 – REVISED JANUARY 2010
 *RoHS Directive 2002/95/EC Jan 27 2003 including Annex.
 Specifications are subject to change without notice.
 Customers should verify actual device performance in their specific applications.

TISP4CxxxH3BJ Overvoltage Protector Series

BOURNS®

Absolute Maximum Ratings, $T_A = 25\text{ }^\circ\text{C}$ (Unless Otherwise Noted)

| Rating | Symbol | Value | Unit |
|---|-------------------|-------------|------------------|
| Repetitive peak off-state voltage | V_{DRM} | '4C115H3BJ | ±90 |
| | | '4C125H3BJ | ±100 |
| | | '4C145H3BJ | ±120 |
| | | '4C165H3BJ | ±135 |
| | | '4C180H3BJ | ±145 |
| | | '4C220H3BJ | ±180 |
| | | '4C250H3BJ | ±190 |
| | | '4C290H3BJ | ±220 |
| Non-repetitive peak impulse current (see Notes 1 and 2) 2/10 μs (GR-1089-CORE, 2/10 μs voltage wave shape) 10/160 μs (TIA-968-A, 10/160 μs voltage wave shape) 5/310 μs (ITU-T K.44, 10/700 μs voltage wave shape used in K.20/21/45) 10/560 μs (TIA-968-A, 10/560 μs voltage wave shape) 10/1000 μs (GR-1089-CORE, 10/1000 μs voltage wave shape) | I_{PPSM} | | ±500 |
| | | | ±200 |
| | | | ±150 |
| | | | ±100 |
| | | | ±100 |
| | | | |
| | | | |
| | | | |
| Non-repetitive peak on-state current (see Notes 1, 2 and 3) 20 ms, 50 Hz (full sine wave) 1000 s, 50 Hz | I_{TSM} | | 30 |
| | | | 2.1 |
| Junction temperature | T_J | -40 to +150 | $^\circ\text{C}$ |
| Storage temperature range | T_{stg} | -65 to +150 | $^\circ\text{C}$ |

- NOTES: 1. Initially the device must be in thermal equilibrium with $T_J = 25\text{ }^\circ\text{C}$.
 2. The surge may be repeated after the device returns to its initial conditions.
 3. EIA/JESD51-2 environment and EIA/JESD51-3 PCB with standard footprint dimensions connected with 5 A rated printed wiring track widths.

Electrical Characteristics, $T_A = 25\text{ }^\circ\text{C}$ (Unless Otherwise Noted)

| Parameter | Test Conditions | Min | Typ | Max | Unit |
|--|--|------------|-----|--|---------------|
| I_{DRM} Repetitive peak off-state current | $V_D = V_{\text{DRM}}$ $T_A = 25\text{ }^\circ\text{C}$ $T_A = 85\text{ }^\circ\text{C}$ | | | ±5 ±10 | μA |
| $V_{(\text{BO})}$ Breakover voltage | $dv/dt = \pm 250\text{ V/ms}$, $R_{\text{SOURCE}} = 300\ \Omega$ | | | ±115 ±125 ±145 ±165 ±180 ±220 ±250 ±290 ±350 | V |
| $V_{(\text{BO})}$ Impulse breakover voltage | $dv/dt \leq \pm 1000\text{ V}/\mu\text{s}$, Linear voltage ramp, Maximum ramp value = ±500 V $di/dt = \pm 10\text{ A}/\mu\text{s}$, Linear current ramp, Maximum ramp value = ±10 A | | | ±125 ±135 ±155 ±175 ±190 ±230 ±260 ±300 ±360 | V |
| $I_{(\text{BO})}$ Breakover current | $dv/dt = \pm 250\text{ V/ms}$, $R_{\text{SOURCE}} = 300\ \Omega$ | | | ±600 | mA |
| V_T On-state voltage | $I_T = \pm 5\text{ A}$, $t_w = 100\ \mu\text{s}$ | | | ±3 | V |
| I_H Holding current | $I_T = \pm 5\text{ A}$, $di/dt = \pm 30\text{ mA/ms}$ | ±150 | | ±600 | mA |
| C_O Off-state capacitance | $f = 1\text{ MHz}$, $V_d = 1\text{ V rms}$, $V_D = -2\text{ V}$ | '4C115H3BJ | | 50 | pF |
| | | '4C125H3BJ | | | |
| | | '4C145H3BJ | | 45 | |
| | | '4C165H3BJ | | | |
| | | '4C180H3BJ | | | |
| | | '4C220H3BJ | | | |
| | | | 40 | | |
| | | | | | |

TISP4CxxxH3BJ Overvoltage Protector Series

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Thermal Characteristics, $T_A = 25\text{ }^\circ\text{C}$ (Unless Otherwise Noted)

| Parameter | Test Conditions | Min | Typ | Max | Unit |
|--|--|-----|-----|-----|--------------------|
| $R_{\theta JA}$ Junction to ambient thermal resistance | EIA/JESD51-3 PCB, $I_T = I_{TSM(1000)}$ (see Note 4) | | | 113 | $^\circ\text{C/W}$ |
| | 265 mm x 210 mm populated line card, 4-layer PCB, $I_T = I_{TSM(1000)}$ | | 50 | | |

NOTE: 4. EIA/JESD51-2 environment and PCB has standard footprint dimensions connected with 5 A rated printed wiring track widths.

Parameter Measurement Information

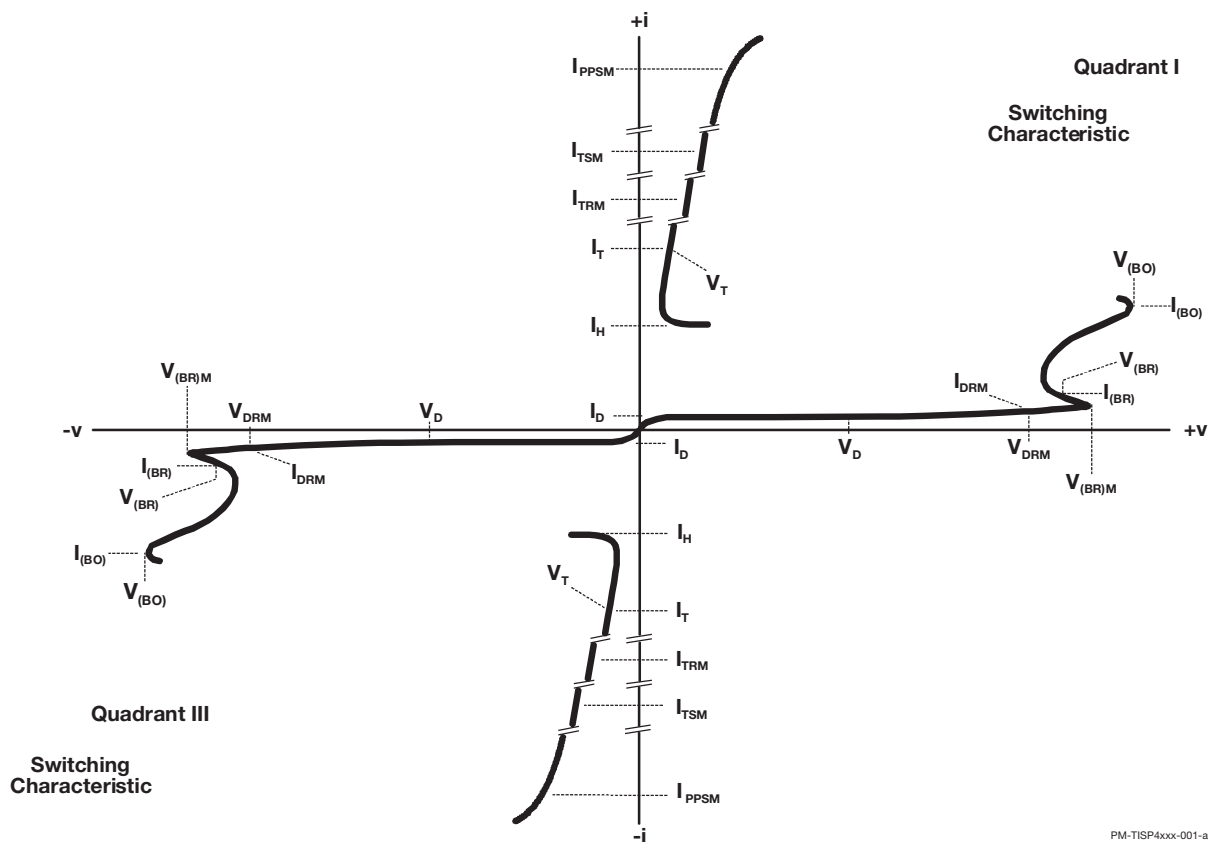
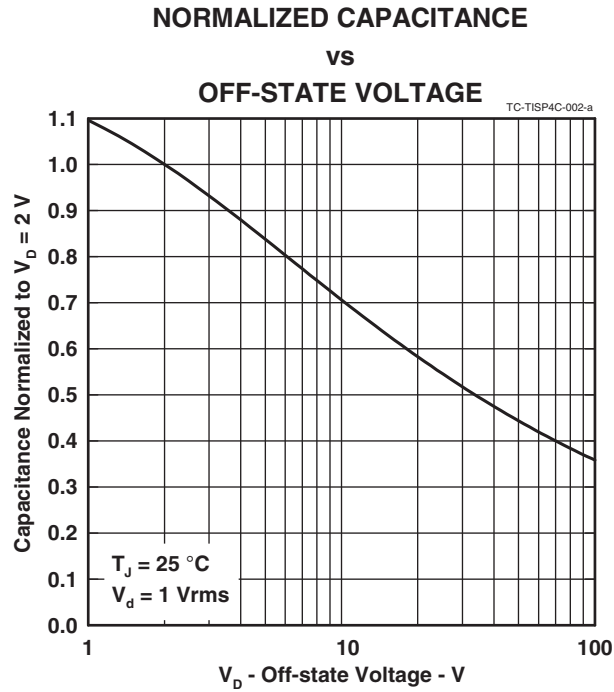


Figure 1. Voltage-Current Characteristic for T and R Terminals
All Measurements are Referenced to the R Terminal

PM-TISP4xxx-001-a

Typical Characteristics



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